MC10216

High Speed Triple Line Receiver

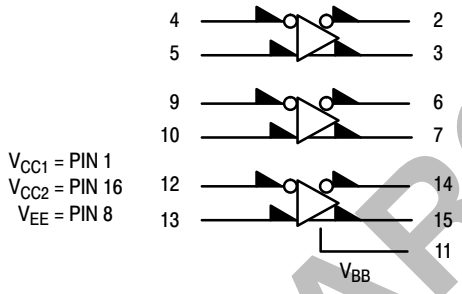
The MC10216 is a high speed triple differential amplifier designed for use in sensing differential signals over long lines. The base bias supply (V_{BB}) is made available at pin 11 to make the device useful as a Schmitt trigger, or in other applications where a stable reference voltage is necessary.

Active current sources provide the MC10216 with excellent common mode noise rejection. If any amplifier in a package is not used, one input of that amplifier must be connected to V_{BB} (pin 11) to prevent upsetting the current source bias network.

Complementary outputs are provided to allow driving twisted pair lines, to enable cascading of several amplifiers in a chain, or simply to provide complement outputs of the input logic function.

- P_D = 100 mW typ/pkg (No Load)
- t_{pd} = 1.8 ns typ (Single ended)
- = 1.5 ns typ (Differential)
- t_r, t_f = 1.5 ns typ (20%–80%)

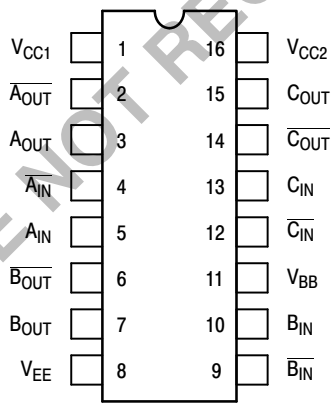
LOGIC DIAGRAM



*V_{BB} to be used to supply bias to the MC10216 only and bypassed (when used) with 0.01 μF to 0.1 μF capacitor.

When the input pin with bubble goes positive, it's respective output pin with bubble goes positive.

DIP PIN ASSIGNMENT

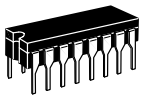


Pin assignment is for Dual–in–Line Package.
For PLCC pin assignment, see the Pin Conversion Tables on page 18 of the ON Semiconductor MECL Data Book (DL122/D).

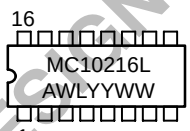
ON Semiconductor

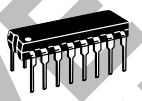
http://onsemi.com

MARKING DIAGRAMS

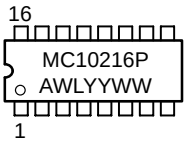


CDIP–16
L SUFFIX
CASE 620

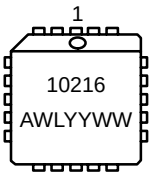




PDIP–16
P SUFFIX
CASE 648



PLCC–20
FN SUFFIX
CASE 775



A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC10216L	CDIP–16	25 Units / Rail
MC10216P	PDIP–16	25 Units / Rail
MC10216FN	PLCC–20	46 Units / Rail

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Pin Under Test	Test Limits							Unit
			–30°C		+25°C			+85°C		
			Min	Max	Min	Typ	Max	Min	Max	
Power Supply Drain Current	I_E	8		27		20	25		27	mAdc
Input Current	I_{inH}	4		180			115		115	μAdc
	I_{CBO}	4 9		1.5 1.5			1.0 1.0		1.0 1.0	μAdc
Output Voltage Logic 1	V_{OH}	2 3	–1.060 –1.060	–0.890 –0.890	–0.960 –0.960		–0.810 –0.810	–0.890 –0.890	–0.700 –0.700	Vdc
Output Voltage Logic 0	V_{OL}	2 3	–1.890 –1.890	–1.675 –1.675	–1.850 –1.850		–1.650 –1.650	–1.825 –1.825	–1.615 –1.615	Vdc
Threshold Voltage Logic 1	V_{OHA}	2 3	–1.080 –1.080		–0.980 –0.980			–0.910 –0.910		Vdc
Threshold Voltage Logic 0	V_{OLA}	2 3		–1.655 –1.655			–1.630 –1.630		–1.595 –1.595	Vdc
Reference Voltage	V_{BB}	11	–1.420	–1.280	–1.350		–1.230	–1.295	–1.150	Vdc
Switching Times (50Ω Load)										ns
Propagation Delay	t_{4+2+} t_{4-2-} t_{4+3-} t_{4-3+}	2 2 3 3	1.0 1.0 1.0 1.0	2.6 2.6 2.6 2.6	1.0 1.0 1.0 1.0	1.8* 1.8* 1.8* 1.8*	2.5 2.5 2.5 2.5	1.0 1.0 1.0 1.0	2.8 2.8 2.8 2.8	
Rise Time (20 to 80%)	t_{2+} t_{3+}	2 3	1.0 1.0	2.6 2.6	1.0 1.0	1.5 1.5	2.5 2.5	1.0 1.0	2.8 2.8	
Fall Time (20 to 80%)	t_{2-} t_{3-}	2 3	1.0 1.0	2.6 2.6	1.0 1.0	1.5 1.5	2.5 2.5	1.0 1.0	2.8 2.8	

* Delay is 1.5ns when inputs are driven differentially.
Delay is 1.8ns when inputs are driven single ended.

ELECTRICAL CHARACTERISTICS (continued)

@ Test Temperature	V_{IHmax}	V_{ILmin}	V_{IHAmin}	V_{ILAmax}	V_{BB}	V_{EE}
–30°C	–0.890	–1.890	–1.205	–1.500	From Pin 11	–5.2
+25°C	–0.810	–1.850	–1.105	–1.475		–5.2
+85°C	–0.700	–1.825	–1.035	–1.440		–5.2

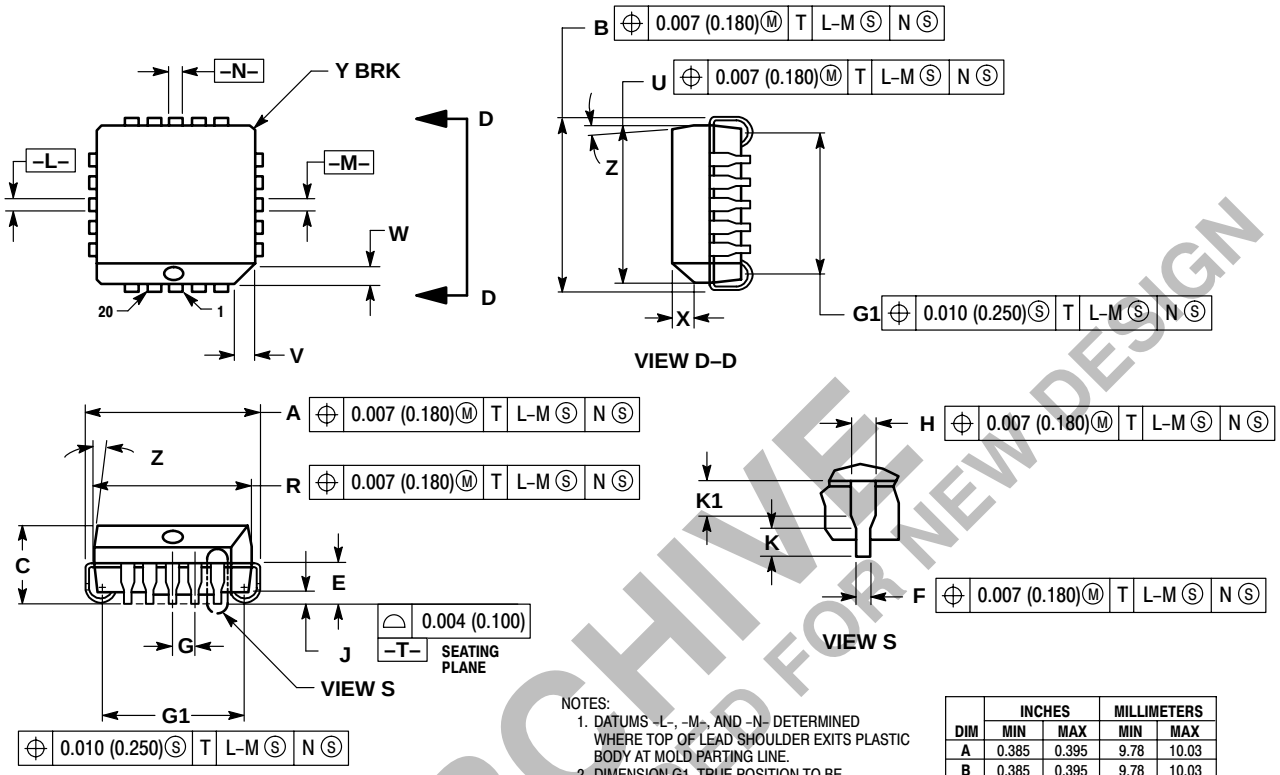
TEST VOLTAGE VALUES (Volts)

Characteristic	Symbol	Pin Under Test	V_{IHmax}	V_{ILmin}	V_{IHAmin}	V_{ILAmax}	V_{BB}	V_{EE}	(V_{CC}) Gnd
			TEST VOLTAGE APPLIED TO PINS LISTED BELOW						
Power Supply Drain Current	I_E	8	4, 9, 12				5, 10, 13	8	1, 16
Input Current	I_{inH}	4	4	9, 12			5, 10, 13	8	1, 16
	I_{CBO}	4 9		9, 12 4, 12			5, 10, 13 5, 10, 13	8, 4 8, 9	1, 16 1, 16
Output Voltage Logic 1	V_{OH}	2 3	4 9, 12	9, 12 4			5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Output Voltage Logic 0	V_{OL}	2 3	9, 12 4	4 9, 12			5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Threshold Voltage Logic 1	V_{OHA}	2 3	 9, 12	9, 12	4	 4	5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Threshold Voltage Logic 0	V_{OLA}	2 3	 9, 12	9, 12	 4	4 	5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Reference Voltage	V_{BB}	11					5, 10, 13	8	1, 16
Switching Times (50Ω Load)					**Pulse In**	**Pulse Out**		**–3.2 V**	**+2.0 V**
Propagation Delay	t_{4+2+}	2			4	2	5, 10, 13	8	1, 16
	t_{4-2-}	2			4	2	5, 10, 13	8	1, 16
	t_{4+3-}	3			4	3	5, 10, 13	8	1, 16
	t_{4-3+}	3			4	3	5, 10, 13	8	1, 16
Rise Time (20 to 80%)	t_{2+}	2			4	2	5, 10, 13	8	1, 16
	t_{3+}	3			4	3	5, 10, 13	8	1, 16
Fall Time (20 to 80%)	t_{2-}	2			4	2	5, 10, 13	8	1, 16
	t_{3-}	3			4	3	5, 10, 13	8	1, 16

Each MECL 10,000 series circuit has been designed to meet the dc specifications shown in the test table, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 500 linear fpm is maintained. Outputs are terminated through a 50–ohm resistor to –2.0 volts. Test procedures are shown for only one gate. The other gates are tested in the same manner.

PACKAGE DIMENSIONS

PLCC–20
FN SUFFIX
PLASTIC PLCC PACKAGE
CASE 775–02
ISSUE C

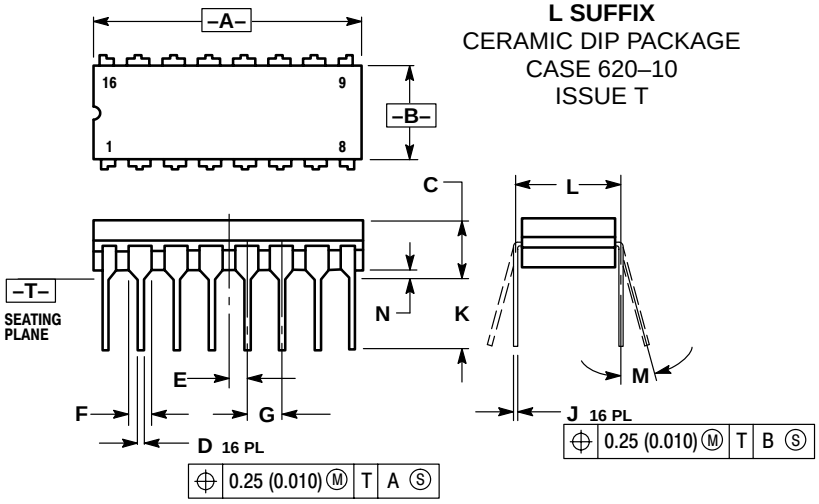


NOTES:
1. DATUMS –L–, –M–, AND –N– DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD PARTING LINE.
2. DIMENSION G1, TRUE POSITION TO BE MEASURED AT DATUM –T–, SEATING PLANE.
3. DIMENSIONS R AND U DO NOT INCLUDE MOLD FLASH. ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
5. CONTROLLING DIMENSION: INCH.
6. THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300). DIMENSIONS R AND U ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
7. DIMENSION H DOES NOT INCLUDE DAMBAR PROTRUSION OR INTRUSION. THE DAMBAR PROTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.385	0.395	9.78	10.03
B	0.385	0.395	9.78	10.03
C	0.165	0.180	4.20	4.57
E	0.090	0.110	2.29	2.79
F	0.013	0.019	0.33	0.48
G	0.050 BSC		1.27 BSC	
H	0.026	0.032	0.66	0.81
J	0.020	---	0.51	---
K	0.025	---	0.64	---
R	0.350	0.356	8.89	9.04
U	0.350	0.356	8.89	9.04
V	0.042	0.048	1.07	1.21
W	0.042	0.048	1.07	1.21
X	0.042	0.056	1.07	1.42
Y	---	0.020	---	0.50
Z	2 °	10 °	2 °	10 °
G1	0.310	0.330	7.88	8.38
K1	0.040	---	1.02	---

PACKAGE DIMENSIONS

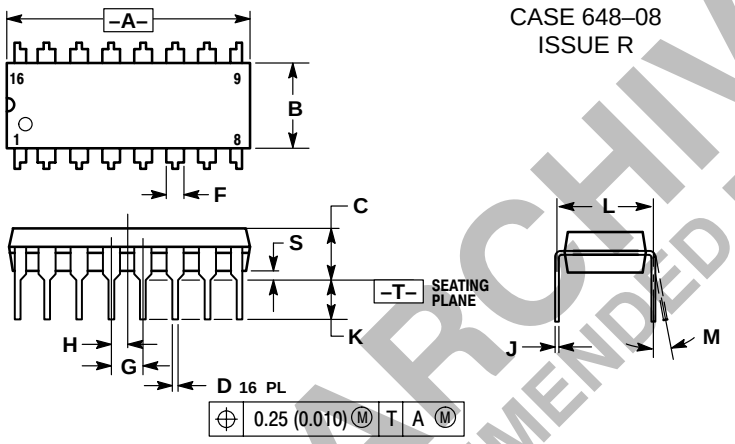
CDIP–16
L SUFFIX
CERAMIC DIP PACKAGE
CASE 620–10
ISSUE T



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.750	0.785	19.05	19.93
B	0.240	0.295	6.10	7.49
C	---	0.200	---	5.08
D	0.015	0.020	0.39	0.50
E	0.050 BSC		1.27 BSC	
F	0.055	0.065	1.40	1.65
G	0.100 BSC		2.54 BSC	
H	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300 BSC		7.62 BSC	
M	0 °	15 °	0 °	15 °
N	0.020	0.040	0.51	1.01

PDIP–16
P SUFFIX
PLASTIC DIP PACKAGE
CASE 648–08
ISSUE R



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.740	0.770	18.80	19.55
B	0.250	0.270	6.35	6.85
C	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54 BSC	
H	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

Notes

Notes

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:
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